

Citations for Ion : **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1959	Guseva, M. I. Inopin, E. V. Tsytko, S. P. 'Depth of Penetration and Character of Distribution of Atoms Injected into Si30 Isotope Targets' <i>Zh. Eksp. Teor. Fiz.</i> , 36, 3-9 (1959) [<i>Engl. Trans. Sov. Phys. JETP</i> , 36, 1-5 (1959)] <i>Comment</i> : R, dR. 10-28 keV 30Si -> Cu, 25 keV 30Si -> Ta	1959-Guse
1963	Bilger, H. Baldinger, E. Czaja, W. 'Ionization von Si-Ruckstosskernen in Si-Zahldioden Bei Bestrahlung Mit Neutronen von 3. Bis 3.9 MeV.' <i>Helv. Phys. Acta</i> , 36, 405-12 (1963) <i>Comment</i> : S, Eta(Epsilon). 430 - 560 keV Si -> Si	1963-Bilg
1964	Sattler, A. R. Silbert, M. G. 'Ionization of Energetic Silicon Atoms Within a Silicon Lattice' <i>Bull. Am. Phys. Soc.</i> , 9, 655-56 (1964) <i>Comment</i> : S. 0.2-3.1 MeV Si -> Si	1964-Satt
1966	Fastrup, B. Hvelplund, P. Sautter, C. A. 'Stopping Cross Section in Carbon of 0.1-1.0 MeV Atoms with 5<Z<20' <i>Kgl. Danske Videnskab. Selskab. Mat. Fys. Medd.</i> , 35, No. 10, 1-28 (1966) <i>Comment</i> : S. (80-900 keV) H, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar->C	1966-Fast
1967	DeCosnac, B. Dulien, P. Noel, J. P. 'Mesure De L'Energie Cedee Au Reseau Par Un Primaire Dans Le Silicium' <i>Rev. Physique Appl.</i> , 2, 158-63 (1967) <i>Comment</i> : S, Eta(Epsilon). 100-400 keV Si -> Si	1967-DeCo
1968	Eisen, F. H. 'Channeling of Medium-Mass Ions through Silicon' <i>Can. J. Phys.</i> , 46, 561-72 (1968) <i>Comment</i> : S. 100-500 keV B, C, N, O, F, Ne, Na, Mg, Al, Si, P, Cl, Ar, K -> Si (Cryst.)	1968-Eise
1969	Bottiger, J. Bason, F. 'Energy Loss of Heavy Ions Along Low-Index Directions in Gold Single Crystals' <i>Rad. Effects</i> , 2, 105-10 (1969) <i>Comment</i> : S. (300-970 keV) N, Ne, Na, Mg, S, Cl, Ar, K, Si, Mn, Fe, Kr, Y, Mo, Ag, Cd, Sb, Xe -> Au	1969-Bott
1969	Macdonald, J. R. Sidenius, G. 'The Total Ionization in Methane of Ions with 1 <= Z1 <= 20 at Energies from 10 to 120 keV' <i>Phys. Letters A</i> , 28, 543-44 (1969) <i>Comment</i> : S. 10-120 keV H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, Ca, V, Sc, Ti -> CH4	1969-Macd
1972	Schwuttke, G. H. Brack, K. Gorey, E. F. Kahan, A. Lowe, L. F. 'Formation and Annealing of Isolation Regions in Silicon through Si Bombardment' <i>Phys. Stat. Sol. A</i> , 14, 107-113 (1972) <i>Comment</i> : R,dR. Si (1 MeV) -> Si One of the earliest MeV implantation papers.	1972-Schw

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1974	Grob, J. J. Grob, A. Siffert, P. 'Evaluation of Heavy Ion Energy Losses in Silicon Due to a Channelling Phenomena' <i>Vide (France), 29, 374-9 (1974)</i> <i>Comment : S, dS. (400-1900 keV) N, Si -> Si</i>	1974-Grob
1975	Grob, J. J. Grob, A. Pape, A. Siffert, P. 'Energy Loss of Heavy Ions in Nuclear Collisions in Silicon' <i>Phys. Rev. B, 11, 3274-79 (1975)</i> <i>Comment : S, dS, Eta(Epsilon). 0.3-2 MeV N, Si -> Si (Cryst.)</i>	1975-Grob
1976	Grob, A. Grob, J. J. Siffert, P. 'Energy Loss and Straggling of Heavy Ions by Nuclear Interactions in Silicon' <i>Nucl. Inst. Methods, 132, 273-79 (1976)</i> <i>Comment : S, dS, Eta(Epsilon). 300-2000 keV C, N, O, Ne, Si, S, Ar -> Si</i>	1976-Grob
1977	Lee, D. H. Malbon, R. M. 'Ion-Implanted Silicon Profiles in GaAs' <i>Appl. Phys. Letters, 30, 327-329 (1977)</i> <i>Comment : R, dR. 50-500 keV Si -> GaAs</i>	1977-Lee
1977	Ndocko-Ndongue, V. B. Pape, A. J. Armbruster, R. 'Low Energy Stopping Powers of Some Heavy Ions in Gold' <i>Rad. Effects, 33, 91-93 (1977)</i> <i>Comment : S. 50-500 keV 4He, 12C, 14N, 16O, 20Ne, 28Si, 40Ar -> Au</i>	1977-Ndoc
1978	Alexander, T. K. Forster, J. S. Ball, G. C. Davies, W. G. Winterbon, K. B. 'Z1 and Z2 Variations in the Stopping Powers of Z1=10-18 Ions Deduced from DSAM Lifetime Measurements' <i>Phys. Letters, 74B, 183-186 (1978)</i> <i>Comment : S. Ne, Na, Mg, Al, Si, P, S, Ar (3-4 MeV) -> Cu, Ni, Ta, Au, Mg, Ca, Ti, Ba. Doppler shift lifetime measurements.</i>	1978-Alex
1978	Kappert, H. F. Heidemann, K. F. Grabe, B. te Kaat, E. 'Range and Damage Profiling after Heavy Ion Implantation in the MeV Region' <i>Phys. Stat. Sol. A, 47, 751 (1978)</i> <i>Comment : R,dR. O, Si (2 MeV) -> Si</i>	1978-Kapp
1979	Andrews, H. R. Lennard, W. N. Mitchell, I. V. Ward, D. Phillips, D. 'Low Energy Stopping Powers Determined by Time of Flight Techniques' <i>IEEE Trans. Nucl. Sci., NS-26, 1326-1330 (1979)</i> <i>Comment : S. (0.180 <vel.< 0.219 cm/ns) (6 <= Z1 <= 20)-> C, Al, Ni, Ag, Au</i>	1979-Andr
1979	Kappert, H. F. Sixt, G. Schwuttke, G. H. 'Minority Carrier Lifetime in Silicon after Ar+ and Si+ Implantation' <i>Phys. Stat. Sol. A, 52, 463-474 (1979)</i> <i>Comment : R, dR. 200 keV Ar, 80 keV Si -> Si</i>	1979-Kapp

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1979	Kasahara, J. Arai, M. Watanabe, N. 'Suppression of Thermal Conversion in Cr-Doped Semi-Insulating GaAs' <i>J. Appl. Phys.</i> , 50, 8229-8231 (1979) <i>Comment</i> : R, dR. 70-130 keV Si -> GaAs	1979-Kasa
1979	Lorenzo, J. P. Davies, D. E. Ryan, T. G. 'Anodic Oxidation and Electrical Carrier Concentration Profiles of Ion-Implanted InP' <i>J. Electrochem. Soc.</i> , 126, 118-121 (1979) <i>Comment</i> : R, dR. 1 MeV S, Si -> InP	1979-Lore
1979	Pham, M. T. 'A Very Simple Method for Profiling the Ion-Implanted Si-Surface' <i>Phys. Stat. Sol. A</i> , 49, 261-265 (1979) <i>Comment</i> : R. 30 keV Si, P, B, Ar, As; 12.2 keV In -> Si	1979-Pham
1979	Tandon, J. L. Nicolet, M-A. Eisen, F. H. 'Silicon Implantation in GaAs' <i>Appl. Phys. Letters</i> , 34, 165-167 (1979) <i>Comment</i> : R, dR. 300 keV Si -> GaAs	1979-Tand
1979	Tsai, M. Y. Day, D. S. Streetman, B. G. Williams, P. Evans, Jr. C. A. 'Recrystallization of Implanted Amorphous Silicon Layers. II. Migration of Fluorine in BF ₂ ⁺ -Implanted Silicon.' <i>J. Appl. Phys.</i> , 50, 188-192 (1979) <i>Comment</i> : R, dR. 50-200 keV 28Si, 25-85 keV 11B, 150 keV BF ₂ -> Si	1979-Tsai
1979	Tsai, M. Y. Streetman, B. G. 'Recrystallization of Implanted Amorphous Silicon Layers. I. Electrical Properties of Silicon Implanted with BF ₂ ⁺ or Si ⁺ B.' <i>J. Appl. Phys.</i> , 50, 183-187 (1979) <i>Comment</i> : R, dR. 34-200 B, BF ₂ , Si -> Si	1979-Tsai2
1979	Ward, D. Andrews, H. R. Mitchell, I. V. Lennard, W. N. Walker, R. B. 'Systematics for the Z1-Oscillation in Stopping Powers of Various Solid Materials' <i>Can. J. Phys.</i> , 57, 645-656 (1979). <i>Comment</i> : S. (vel.=0.18-0.22 cm/ns) C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Ca -> C, Al, Ni, Ag, Au	1979-Ward
1980	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. 'Charge-Exchange Effects in Energy-Loss Straggling' <i>Nucl. Inst. Methods</i> , 170, 221-225 (1980) <i>Comment</i> : R, dR. 0-50 MeV Atomic Numbers 1-16 -> Al	1980-Sofi
1981	Anthony, J. M. Lanford, W. A. 'Higher Order Z1 Effects in Heavy Ion Stopping Powers and Ranges' <i>Nucl. Inst. Methods</i> , 186, 647-654 (1981) <i>Comment</i> : S, R. Si, Ni, Au (1-2.5 MeV/amu) -> Cu, Ag, Pb	1981-Anth

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1981	Anthony, J. M. Parker, P. D. Lanford, W. A. 'Z1*3, Z1*4 Corrections to Heavy Ion Energy Loss' <i>IEEE Trans. Nucl. Sci., NS-28, 1227-1229 (1981)</i> <i>Comment : S. Si, Cl, Ti, Fe, Ni, Ge, Br (0.4-2.5 MeV/amu) -> Cu, Ag</i>	1981-Anth2
1982	Anthony, J. M. Lanford, W. A. 'Stopping Power and Effective Charge of Heavy Ions in Solids' <i>Phys. Rev. A, 25 (4), 1868-1879 (1982)</i> <i>Comment : S. C, Si, Cl, Ti, Fe, Ni, Ge, Br, Nb, I (0.1-3.5 MeV/amu) -> C, Al, Cu, Ag, Au</i>	1982-Anth
1983	Mannsperger, H. Kalbitzer, S. Demond, F. J. Damjantschitsch, H. 'Projection Factors of Low Energy Ion Ranges' <i>Nucl. Inst. Methods, 209/210, 49-55 (1983)</i> <i>Comment : R. H, C, Na, Al, Si, Ar, Cr (.04<epsilon<1) -> Si, Ge</i>	1983-Mann
1985	Shima, K. 'Charge States of Fast Heavy Ions in Solids- Target Atomic Number Dependence' <i>Nucl. Inst. Methods, B10/11, 45-48 (1985)</i> <i>Comment : S. F, Si, Cl, Cu (29-117 MeV) -> 20 metal foils (charge state analysis)</i>	1985-Shim
1986	Lennard, W. N. Geissel, H. Phillips, D. Jackson, D. P. 'Heavy Ion Straggling: Possible Evidence for Inner-Shell Excitation' <i>Phys. Rev. Letters, 57, 318-320 (1986)</i> <i>Comment : dS.F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Sc (16 keV/amu) -> C</i>	1986-Lenn
1987	Keinonen, J. Kuronen, A. Hautala, M. Karttunen, V. Lappalainen, R. 'Velocity Dependence in Low-Velocity Electronic Stopping Power of Heavy Ions' <i>Phys. Letters A, 123 (6), 307-310 (1987)</i> <i>Comment : S, R, Al, Si (100-820 keV) -> Ta (Ranges at 5, 12 MeV)</i>	1987-Kein
1988	Wilson, R. G. '(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe' <i>J. Appl. Phys., 63, 5302-5311 (1988)</i> <i>Comment : R, dR. 45 Ions (H to Ta) at 100-700 keV -> HgCdTe</i>	1988-Wils
1988	Wilson, R. G. 'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe' <i>J. Crystal Growth, 86, 735-743 (1988)</i> <i>Comment : R, dR. 52 Ions (H-Hg) at 100-700 keV -> CdTe, HgCdTe</i>	1988-Wils2
1989	Tikkanen, P. 'Electronic Stopping Power of Ta for Z=11-18 Atoms at Energies 0-0.8 MeV/amu' <i>Nucl. Inst. Methods, B36, 103 (1989)</i> <i>Comment : S. Na, Mg, Al, Si, P, S, Cl, Ar (0-0.8 MeV/amu) -> Ta</i>	1989-Tikk

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1990	Kumar, S. Sharma, S. K. Garg, A. K. Sharma, A. P. 'Experimental Range of Heavy Ions of Charge 6-28 in CR-39 and Lexan' <i>Appl. Rad. Isotopes (UK), 41, 497-500 (1990)</i> <i>Comment : R. C, N, O, Ne, Si, Fe, Ni (6-9 MeV/amu) -> CR-39, Lexan</i>	1990-Kuma
1990	Raisanen, J. Rauhala, E. 'Stopping Powers and Energy Loss of Mylar, Kapton, Havar and Ni for 10 Ions (Z= 3-17) in the Energy Range 0.2-2.1 MeV/amu' <i>Phys. Rev. B, 41, 3951-3958 (1990)</i> <i>Comment : S. B, C, N, O, Al, Si, P, Cl (0.2-2.1 MeV/amu) -> Mylar, Kapton, Havar, Ni</i>	1990-Rais
1991	Hecking, N. 'Ranges and Electronic Stopping Powers of 1-20 MeV Si Ions in Si Targets as Obtained from Optical Reflectivity Measurements on Bevelled Samples' <i>Nucl. Inst. Methods, B59/60, 619-622 (1991)</i> <i>Comment : S,R. Si (1-20 MeV) -> Si</i>	1991-Heck
1991	Kuronen, A. 'A Study of Stopping Power using Nuclear Methods' <i>Comm. Physico-Math. (Finland), 122, 1-36 (1991)</i> <i>Comment : S. Ion [Z=3-22] at (0-0.4 Vo) -> Solids (Z=14-82)</i>	1991-Kuro
1992	Gunzler, R. Weiser, M. Kalbitzer, S. '3-D Concentration Distributions of Ion Implants' <i>Nucl. Inst. Methods, B62, 350-355 (1992)</i> <i>Comment : R. H, N, Si (.1-6 MeV) -> Ge. 3-D profiles.</i>	1992-Gunz
1992	Keinonen, J. Arstila, K. Tikkanen, P. 'Electronic Stopping Power of Si and Ge for MeV Energy Si Ions' <i>Appl. Phys. Letters, 60, 228-230 (1992)</i> <i>Comment : S. Si, P (0-30 MeV) -> Si, Ge</i>	1992-Kein
1994	Jakob, G. Cub, J. Speidel, K. H. Kremeyer, S. Busch, H. 'On the Ion Beam Stopping Power Dependence of Transient Magnetic Fields in Fe- and Gd- Hosts' <i>Z. Physik D, 32, 7-11 (1994)</i> <i>Comment : S. Mg, Si, Ti -> Fe and Gd compounds</i>	1994-Jako
1994	Raisanen, J. Rauhala, E. Fulop, Z. Kiss, A. Z. Somorjai, E. 'Stopping Powers of CR-39 Nuclear Track Material for Z=1-14 Ions with 0.25-2.8 MeV/amu' <i>Rad. Meas. (UK), 23, 749-752 (1994)</i> <i>Comment : S. Z=1-14 (0.25-2.8 MeV/amu) -> CR-39</i>	1994-Rais2
1995	Arstila, K. Keinonen, J. Tikkanen, P. 'Stopping Pwer for Low Velocity Heavy Ions: Si Ions (0.01-0.9 MeV/amu) in 18 (Z=13-79) Metals' <i>Nucl. Inst. Methods, B101, 321-326 (1995)</i> <i>Comment : S. Si (0.01-0.9 MeV/amu) -> 18 Metals (Z=13-79)</i>	1995-Arst

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1995	Norlund, K. Keinonen, J. Rauhala, E. Ahlgren, T. 'Range Profiles in Self-Implanted Crystalline Si' <i>Phys. Rev., B52, 15170-15175 (1995)</i> <i>Comment : R. Si (50-100 keV) -> Si</i>	1995-Norl
1995	Randhawa, G. S. Garg, A. K. Virk, H. S. 'Range Study of Heavy Ions in Plastic Track Detectors' <i>Rad. Meas. (UK), 24, 197-199 (1995)</i> <i>Comment : R. Heavy Ions (10-17 MeV/amu) -> Lexan</i>	1995-Rand
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. 'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions' <i>Nucl. Inst. Methods, B115, 315-318 (1996)</i> <i>Comment : S. Channeling of ions He to Kr in Si <110></i>	1996-Gelf
1996	Hari, K. V. Pathak, A. P. Sharma, S. K. Shyam, K. Nath, N. 'Energy Loss of MeV Heavy Ions in Carbon' <i>Nucl. Inst. Methods, B108, 223-226 (1996)</i> <i>Comment : S. Zl (O - Cu) at 0.1-1.0 MeV/amu -> C</i>	1996-Hari
1997	Harikumar, V. Pathak, A. P. Nath, N. Kumar, S. Sharma, S. K. 'Stopping Power of Carbon for Se, Fe, Ni and Cu Ions using the ERDA Technique' <i>Nucl. Inst. Methods, B129, 143-146 (1997)</i> <i>Comment : S. Si, Fe, Ni, Cu (Vo - 5Vo) -> C</i>	1997-Hari
2000	Arstila, K. 'An Experimental Method for Precise Determination of Electronic Stopping Powers for Heavy Ions' <i>Nucl. Inst. Methods, B168, 473-483 (2000)</i> <i>Comment : S. Si -> SiO2, Si, ZrO2, Zr, Al2O3, Al</i>	2000-Arst
2000	Shen, Y. Lu, X. Xia, Z. Shen, D. Jiang, D. 'Stopping Powers of Al for MeV Si Ions' <i>Nucl. Inst. Methods, B160, 11-15 (2000)</i> <i>Comment : S. Si (0.8 - 6.4 MeV) -> Al</i>	2000-Shen
2001	Zhang, Y. Possnert, G. Whitlow, H. J. 'Measurements of the Mean Energy-Loss of Swift Heavy Ions in Carbon with High Precision' <i>Nucl. Inst. Methods, B183, 34-37 (2001)</i> <i>Comment : S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, Cr, Mn, Fe (100 - 800 keV/u) -> C</i>	2001-Zhan
2002	Trzaska, W. H. Lyapin, V. Alanko, T. Mutterer, M. Raisanen, J. 'New Approach to Energy Loss Measurements' <i>Nucl. Inst. Methods, B195, 147-165 (2002)</i> <i>Comment : S. Ar, Si, O, He, H -> Au, Ni, C, Havar</i>	2002-Trza

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2002	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T.D.M. Zhang, Y. 'Measurements of Si Ion Stopping in Amorphous Silicon' <i>Nucl. Inst. Methods, B190, 84-88 (2002)</i> <i>Comment : S, Si -> Si</i>	2002-Whit
2002	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T. D. Zhang, Y. 'Measurement and Uncertianties of Energy Loss in Silicon over a Wide Z1 Range using Time-of-Flight Detector Telescopes' <i>Nucl. Inst. Methods, B195, 133-146 (2002)</i> <i>Comment : S, Li, Be, B, C, N, O, F, Na, Mg, Al, Si, P, Mn, Fe -> Si</i>	2002-Whit2
2002	Zhang, Y. 'High-Precision Measurement of Electronic Stopping Powers for Heavy Ions using High-Resolution Time-of-Flight Spectrometry' <i>Nucl. Inst. Methods, B196, 1-15 (2002)</i> <i>Comment : S. Stopping of 18 Heavy Ions into C, Al and Au Targets</i>	2002-Zhan
2004	Nigam, M. Duggan, J.L. Bounanani, M. El. Yang, C. Ravi, G. V. 'Stopping power of thin GaAs films for Si and P ions' <i>Nucl.Instrum.Methods B219-220, 273 (2004)</i> <i>Comment : S. Si, P (0.07 - 0.3 MeV/n) -> GaAs</i>	2004-Niga
2004	Zhang, Y. Weber, W. Whitlow, H. J. 'Electronic Stopping Powers for Heavy Ions in Silicon' <i>Nucl. Inst. Methods, B215, 48-56 (2004)</i> <i>Comment : S. 14 light ions (Be-Cu) -> Si</i>	2004-Zha3
2005	Tripathy, S. P. Mishra, R. Dwivedi, K. K. 'S.P.Tripathy,R.Mishra,K.K.Dwivedi' <i>Rad. Measurements 40, 255 (2005)</i> <i>Comment : S. 28Si (0.35 - 3.93 MeV/n) -> polycarbonate</i>	2005-Trip
2005	Zhang, Yanwen Weber, W. J. McCready, D.E. Grove, D.A. Jensen, J. 'Experimental determination of electronic stopping for ions in silicon dioxide' <i>Appl. Phys. Lett. 87, 104103 (2005)</i> <i>Comment : S. Be - Si (0.05 - 1.3 MeV/n) -> SiO2</i>	2005-Zha2
2008	Pratibha, Sharma, V. Diwan, P.K. Kumar, S. Khan, S.A. 'Energy loss and stragging in LR-115 and Kapton polymeric foils for energetic ions' <i>Nucl. Instrum. Methods B 266, 2556 (2008)</i> <i>Comment : S, dS, Li, C, O, Si (1.0-6.5 MeV/u) -> LR-115, Kapton</i>	2008-Prat
2008	Sharma, V. Diwan, P.K. Pratibha, Kumar, S. Khan, S.A. 'Stopping power of polymeric foils for swift heavy ions.' <i>Nucl. Instrum. Methods B 266, 3988 (2008)</i> <i>Comment : S. Si, Cl, Ti (1.0-4.5 MeV/u) -> polypropylene, polyethylene naphthalate (PEN)</i>	2008-Shar

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2009	Msimanga, M. Comrie, C.M. Vineda-Vargas, C.A. Murray, S. Bark, R. 'A time of flight-energy spectrometer for stopping power measurements in heavy ion-ERD analysis at iThemba LABS ' <i>Nucl. Instrum. Methods B 267, 2671 (2009)</i> <i>Comment : S. Kr (0.075-0.25 MeV/u), Si (0.22-0.45 MeV/u) -> ZrO2</i>	2009-Msim
